storing in said second register said second data input from the outside of said non-volatile semiconductor memory device; and

writing said second data stored in said second register to said memory cell.

Please add new Claims 18-23 as follows:

--18. The method according to claim 14, wherein

said step of reading said another part of said plurality of data is performed after said step of reading said part of said plurality of data.

19. The method according to claim 18, wherein

said step of outputting said another part of said plurality of data is performed after said step of outputting said part of said plurality of data.

20. The method according to claim 15, wherein

said step of reading said second data is performed after said step of reading said first data.

21. The method according to claim 20, wherein

said step of outputting said second data is performed after said step of outputting said first data.